

## TIP145T/146T/147T

### Monolithic Construction With Built In Base-Emitter Shunt Resistors

- High DC Current Gain :  $h_{FE} = 1000 @ V_{CE} = -4V, I_C = -5A$  (Min.)
- Industrial Use
- Complement to TIP140T/141T/142T

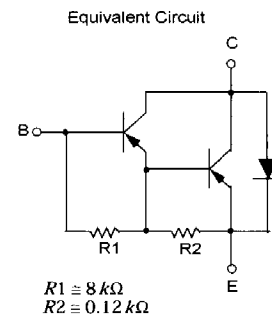


1 TO-220  
1.Base 2.Collector 3.Emmitter

### PNP Epitaxial Silicon Darlington Transistor

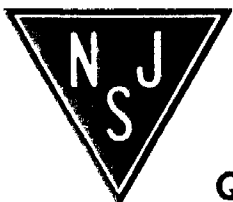
#### Absolute Maximum Ratings $T_C = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	: TIP145T	- 60 V
		: TIP146T	- 80 V
		: TIP147T	- 100 V
$V_{CEO}$	Collector-Emitter Voltage	: TIP145T	- 60 V
		: TIP146T	- 80 V
		: TIP147T	- 100 V
$V_{EBO}$	Emitter-Base Voltage	- 5	V
$I_C$	Collector Current (DC)	- 10	A
$I_{CP}$	Collector Current (Pulse)	- 15	A
$I_B$	Base Current (DC)	- 0.5	A
$P_C$	Collector Dissipation ( $T_C = 25^\circ C$ )	80	W
$T_J$	Junction Temperature	150	$^\circ C$
$T_{STG}$	Storage Temperature	- 65 ~ 150	$^\circ C$



#### Electrical Characteristics $T_C = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
$V_{CEO(sus)}$	Collector-Emitter Sustaining Voltage	$I_C = -30mA, I_B = 0$	- 60			V
			- 80			V
			- 100			V
$I_{CEO}$	Collector Cut-off Current	$V_{CE} = -30V, I_B = 0$ $V_{CE} = -40V, I_B = 0$ $V_{CE} = -50V, I_B = 0$			- 2	mA
					- 2	mA
					- 2	mA
$I_{CBO}$	Collector Cut-off Current	$V_{CB} = -60V, I_E = 0$ $V_{CB} = -80V, I_E = 0$ $V_{CB} = -100V, I_E = 0$			- 1	mA
					- 1	mA
					- 1	mA
$I_{EBO}$	Emitter Cut-off Current	$V_{BE} = -5V, I_C = 0$			- 2	mA
$h_{FE}$	DC Current Gain	$V_{CE} = -4V, I_C = -5A$ $V_{CE} = -4V, I_C = -10A$	1000 500			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -5A, I_B = -10mA$ $I_C = -10A, I_B = -40mA$			- 2	V
					- 3	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -10A, I_B = -40mA$			- 3.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$V_{CE} = -4V, I_C = -10A$			- 3	V
$t_D$	Delay Time	$V_{CC} = -30V, I_C = -5A$ $I_{B1} = -20mA, I_{B2} = 20mA$ $R_L = 6\Omega$		0.15		$\mu s$
$t_R$	Rise Time			0.55		$\mu s$
$t_{STG}$	Storage Time			2.5		$\mu s$
$t_F$	Fall Time			2.5		$\mu s$



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors

# TO-220

